National Semiconductor is now part of

Texas Instruments.

Search <u>http://www.ti.com/</u> for the latest technical

information and details on our current products and services.

August 2005



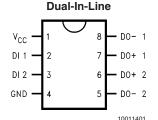
DS90LV027A LVDS Dual High Speed Differential Driver General Description Features

The DS90LV027A is a dual LVDS driver device optimized for high data rate and low power applications. The device is designed to support data rates in excess of 600Mbps (300MHz) utilizing Low Voltage Differential Signaling (LVDS) technology. The DS90LV027A is a current mode driver allowing power dissipation to remain low even at high frequency. In addition, the short circuit fault current is also minimized.

The device is in a 8-lead small outline package. The DS90LV027A has a flow-through design for easy PCB layout. The differential driver outputs provides low EMI with its typical low output swing of 360 mV. It is perfect for high speed transfer of clock and data. The DS90LV027A can be paired with its companion dual line receiver, the DS90LV028A, or with any of National"s LVDS receivers, to provide a high-speed point-to-point LVDS interface.

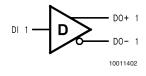
- >600 Mbps (300MHz) switching rates
- 0.3 ns typical differential skew
- 0.7 ns maximum differential skew
- 1.5 ns maximum propagation delay
- 3.3V power supply design
- ±360 mV differential signaling
- Low power dissipation (46 mW @ 3.3V static)
- Flow-through design simplifies PCB layout
- Interoperable with existing 5V LVDS devices
- Power Off Protection (outputs in high impedance)
- Conforms to TIA/EIA-644 Standard
- 8-Lead SOIC package saves space
- Industrial temperature operating range (-40°C to +85°C)

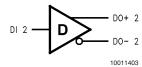
Connection Diagram



Order Number DS90LV027ATM See NS Package Number M08A

Functional Diagram





Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.3V to +4V
Input Voltage (DI)	-0.3V to +3.6V
Output Voltage (DO±)	-0.3V to +3.9V
Maximum Package Power Dissi	pation @ +25°C
M Package	1190 mW
Derate M Package	9.5 mW/°C above +25°C
Storage Temperature Range	−65°C to +150°C
Lead Temperature Range Solde	ering
(4 sec.)	+260°C

ESD Ratings

$\ge 8 \text{kV}$
≥ 1000V
≥ 1000V
$\geq 4kV$

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage (V_{CC})	3.0	3.3	3.6	V
Temperature (T _A)	-40	25	+85	°C

Electrical Characteristics

Over Supply Voltage and Operating Temperature ranges, unless otherwise specified. (Notes 2, 3, 7)

Symbol	Parameter	Co	onditions	Pin	Min	Тур	Мах	Units
DIFFERENTIAL DRIVER CHARACTERISTICS								
V _{OD}	Output Differential Voltage	$R_L = 100\Omega$	R _L = 100Ω		250	360	450	mV
ΔV_{OD}	V _{OD} Magnitude Change	(Figure 1)		DO-		1	35	mV
V _{OH}	Output High Voltage					1.4	1.6	V
V _{OL}	Output Low Voltage]			0.9	1.1		V
Vos	Offset Voltage	1			1.125	1.2	1.375	V
ΔV_{OS}	Offset Magnitude Change				0	3	25	mV
IOXD	Power-off Leakage	$V_{OUT} = V_{CC}$ or GND, $V_{CC} = 0V$		1		±1	±10	μA
IOSD	Output Short Circuit Current			1		-5.7	-8	mA
V _{IH}	Input High Voltage			DI	2.0		V _{cc}	V
V _{IL}	Input Low Voltage			1	GND		0.8	V
I _{IH}	Input High Current	V _{IN} = 3.3V or 2.4V		1		±2	±10	μA
I	Input Low Current	V _{IN} = GND or 0.5V		1		±1	±10	μA
V _{CL}	Input Clamp Voltage	I _{CL} = -18 mA		1	-1.5	-0.6		V
I _{CC}	Power Supply Current	No Load	$V_{IN} = V_{CC}$ or GND	V _{cc}		8	14	mA
		$R_L = 100\Omega$				14	20	mA

Switching Characteristics

Over Supply Voltage and Operating Temperature Ranges, unless otherwise specified. (Notes 3, 4, 5, 6)

Symbol	Parameter	Conditions	Min	Тур	Мах	Units
DIFFEREN	DIFFERENTIAL DRIVER CHARACTERISTICS					
t _{PHLD}	Differential Propagation Delay High to Low	$R_{L} = 100\Omega, C_{L} = 15 \text{ pF}$	0.3	0.8	1.5	ns
t _{PLHD}	Differential Propagation Delay Low to High	(Figure 2 and Figure 3)	0.3	1.1	1.5	ns
t _{sKD1}	Differential Pulse Skew It _{PHLD} – t _{PLHD} I (Note 8)		0	0.3	0.7	ns
t _{SKD2}	Channel to Channel Skew (Note 9)		0	0.4	0.8	ns
t _{SKD3}	Differential Part to Part Skew (Note 10)		0		1.0	ns
t _{SKD4}	Differential Part to Part Skew (Note 11)]	0		1.2	ns
t _{TLH}	Transition Low to High Time]	0.2	0.5	1.0	ns
t _{THL}	Transition High to Low Time]	0.2	0.5	1.0	ns
f _{MAX}	Maximum Operating Frequency (Note 12)]		350		MHz

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" specifies conditions of device operation.

Note 2: Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except V_{OD}.

Note 3: All typicals are given for: V_{CC} = +3.3V and T_A = +25 $^\circ C.$

Note 4: These parameters are guaranteed by design. The limits are based on statistical analysis of the device over PVT (process, voltage, temperature) ranges. Note 5: C_L includes probe and fixture capacitance.

Switching Characteristics (Continued)

Note 6: Generator waveform for all tests unless otherwise specified: f = 1 MHz, $Z_O = 50\Omega$, $t_r \le 1$ ns, $t_f \le 1$ ns (10%-90%).

Note 7: The DS90LV027A is a current mode device and only function with datasheet specification when a resistive load is applied to the drivers outputs.

Note 8: t_{SKD1}, It_{PHLD} - t_{PLHD}|, is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.

Note 9: t_{SKD2} is the Differential Channel to Channel Skew of any event on the same device.

Note 10: t_{SKD3} , Differential Part to Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V_{CC} and within 5°C of each other within the operating temperature range.

Note 11: t_{SKD4}, part to part skew, is the differential channel to channel skew of any event between devices. This specification applies to devices over recommended operating temperature and voltage ranges, and across process distribution. t_{SKD4} is defined as IMax – MinI differential propagation delay.

Note 12: f_{MAX} generator input conditions: $t_r = t_f < 1$ ns (0% to 100%), 50% duty cycle, 0V to 3V. Output criteria: duty cycle = 45%/55%, $V_{OD} > 250$ mV, all channels switching.

Parameter Measurement Information

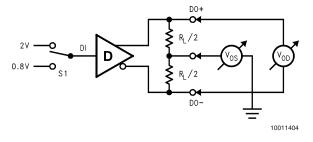


FIGURE 1. Differential Driver DC Test Circuit

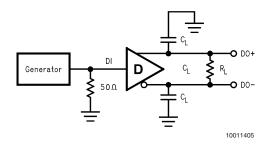
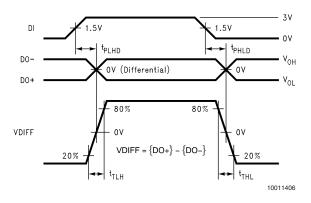
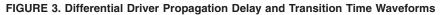


FIGURE 2. Differential Driver Propagation Delay and Transition Time Test Circuit



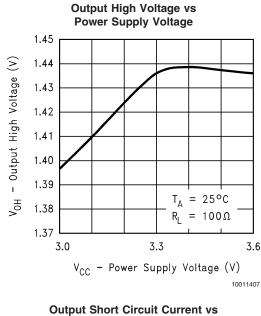


Application Information

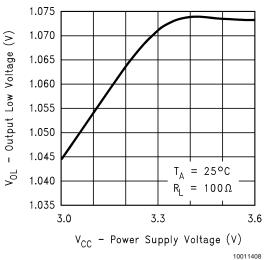
Pin #	Name	Description
2, 3	DI	TTL/CMOS driver input pins
6, 7	DO+	Non-inverting driver output pin
5, 8	DO-	Inverting driver output pin
4	GND	Ground pin
1	V _{cc}	Positive power supply pin, $+3.3V \pm 0.3V$

TABLE 1. Device Pin Descriptions

Typical Performance Curves



Output Low Voltage vs Power Supply Voltage



Differential Output Voltage vs Power Supply Voltage

